K-Band Via-Hole Grounding pi-Gate FET With Monolithic On-Chip Matching Network

P. Saunier and S. Nelson. "K-Band Via-Hole Grounding pi-Gate FET With Monolithic On-Chip Matching Network." 1983 MTT-S International Microwave Symposium Digest 83.1 (1983 [MWSYM]): 268-269.

A 1650 µm gate width GaAs FET with monolithic partial on-chip matching network of the input for broadband operation had 630 mW output power with 4 dB gain from 17 to 20.5 GHz. The pi-gate design includes 13 reactive-ion-etched source vias on a 50 µm substrate with a plated heat sink.

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